



Product data sheet

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SOD-' 23



BAT46WG SCHOTTKY BARRIER DIODE

FEATURES

- High breakdown voltage
- Low turn-on voltage
- Guard ring construction for transient protection

Maximum Ratings @T₂=25℃

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage		100	V
Working peak reverse voltage	V _{RWM}		
Forward continuous current	Ι _F	150	mA
Repetitive peak forward current (Note 1) @ tp < 1.0s, Duty Cycle < 50%	I _{FRM}	350	mA
Non-repetitive Peak Forward surge current @ t = 8.3ms	I _{FSM}	750	mA
Power dissipation	PD	200	mW
Thermal resistance junction to ambient air	$R_{ extsf{ heta}JA}$	500	°C/W
Operating Junction Temperature Range	Tj	-40 ~ +125	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Reverse breakdown voltage(Note 2)	V _R	I _R = 100μΑ	100			V
Reverse voltage leakage current	I _R	V _{R1} =1.5V			0.3	μΑ
		V _{R2} =10V			0.5	
		V _{R3} =50V			1	
		V _{R4} =75V			2	
Forward voltage(Note 2)	VF	I _{F1} =0.1mA			0.25	V
		I _{F2} =10mA			0.45	
		I⊧3 =250mA			1	
Diode capacitance		V _R =0, f=1MHz		20		
	CT	V _R =1V, f=1MHz		12		p⊢

Notes: 1. Part mounted on FR-4 board with recommended pad layout.

2. Short duration pulse test used to minimize self-heating effect.









PACKAGE MECHANICAL DATA





<u>A1</u>



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A		1.000		0.039	
A1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
с	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
E	1.600	1.800	0.063	0.071	
E1	2.550	2.750	0.100	0.108	
L	0.475 REF.		0.019 REF.		
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAT46WS	SOD-323	3000





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